

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	1
Thermal characteristics						
Thermal resistance, junction - case	R_{thJC}		-	-	1.25	K/W
Thermal resistance, junction - ambient	R_{thJA}	Thermal resistance, junction- ambient, leaded	-	-	62	
Electrical characteristics, at T_j =25	°C, unless	otherwise specified				
Static characteristics						
DC blocking voltage	V _{DC}	I _R =0.05 mA, T _j =25 °C	600	-	-	V
Diode forward voltage	V _F	I _F =10 A, T _j =25 °C	-	1.8	2.1	
		I _F =10 A, T _j =150 °C	-	2.2	-	
Reverse current	I _R	V _R =600 V, T _j =25 °C	-	0.8	90	μΑ
		V _R =600 V, T _j =150 °C	-	3.3	860	
AC characteristics						
Total capacitive charge	Q _c	V_R =400 V, $I_F \le I_{F,max}$, d I_F /d t =200 A/ μ s, T_j =150 °C	-	16	-	nC
Switching time ³⁾	t _c		-	-	<10	ns
Total capacitance	С	V _R =1 V, <i>f</i> =1 MHz	-	290	-	pF
		V _R =300 V, <i>f</i> =1 MHz	-	40	-	1

 V_R =600 V, f=1 MHz

40

¹⁾ J-STD20 and JESD22

²⁾ All devices tested under avalanche conditions, for a time periode of 10ms, at 20mA.

 $^{^{3)}}$ t_c is the time constant for the capacitive displacement current waveform (independent from T_j , I_{LOAD} and di/dt), different from t_{rr} which is dependent on T_j , I_{LOAD} and di/dt. No reverse recovery time constant t_{rr} due to absence of minority carrier injection.

 $^{^{4)}}$ Under worst case Z_{th} conditions.

⁵⁾ Only capacitive charge occuring, guaranteed by design.



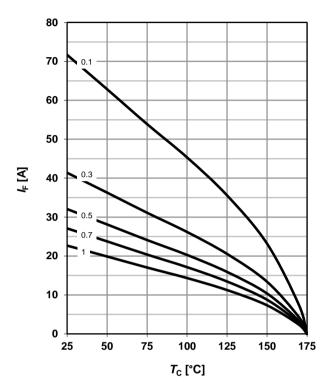
1 Power dissipation

 P_{tot} =f(T_C); parameter: $R_{thJC(max)}$

120 100 80 80 40 20

2 Diode forward current

 $I_F = f(T_C)^{4}$; $T_i \le 175$ °C; parameter: $D = t_p/T$



3 Typ. forward characteristic

50

75

100

*T*_C [°C]

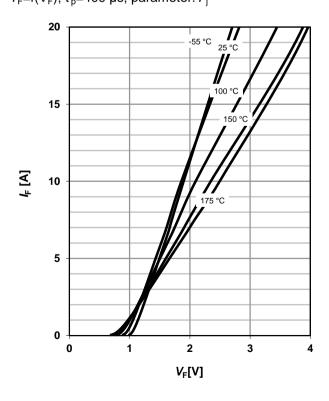
125

150

175

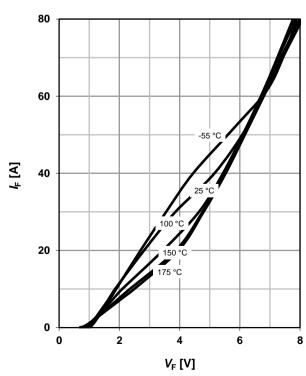
25

 $I_F = f(V_F)$; $t_p = 400 \mu s$; parameter: T_i



4 Typ. forward characteristic in surge current mode

 $I_F=f(V_F)$; $t_p=400 \mu s$; parameter: T_i



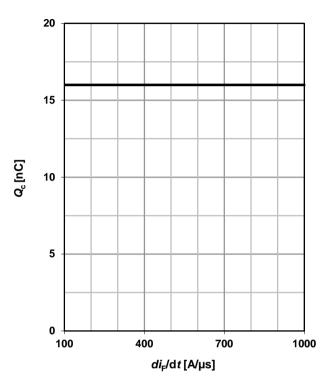


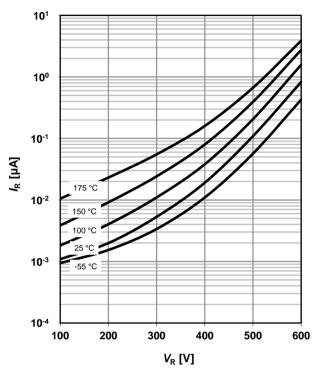
5 Typ. capacitance charge vs. current slope

$Q_C = f(di_F/dt)^{5}$; $I_F \le I_{F,max}$

6 Typ. reverse current vs. reverse voltage

 $I_R=f(V_R)$; parameter: T_i



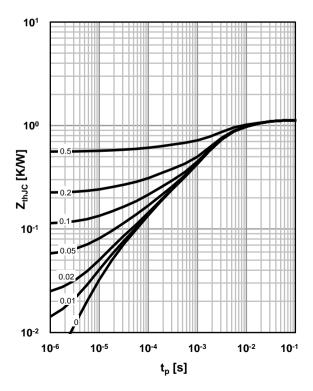


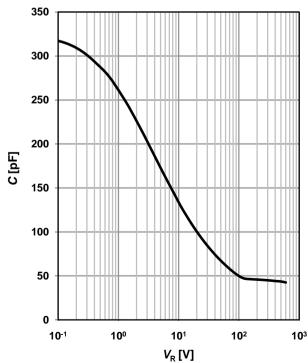
7 Typ. transient thermal impedance

 Z_{thJC} =f(t_p); parameter: $D = t_P/T$

8 Typ. capacitance vs. reverse voltage

 $C=f(V_R)$; $T_C=25$ °C, f=1 MHz

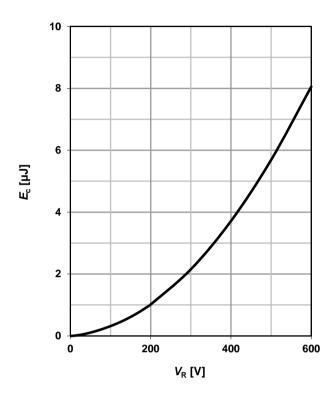






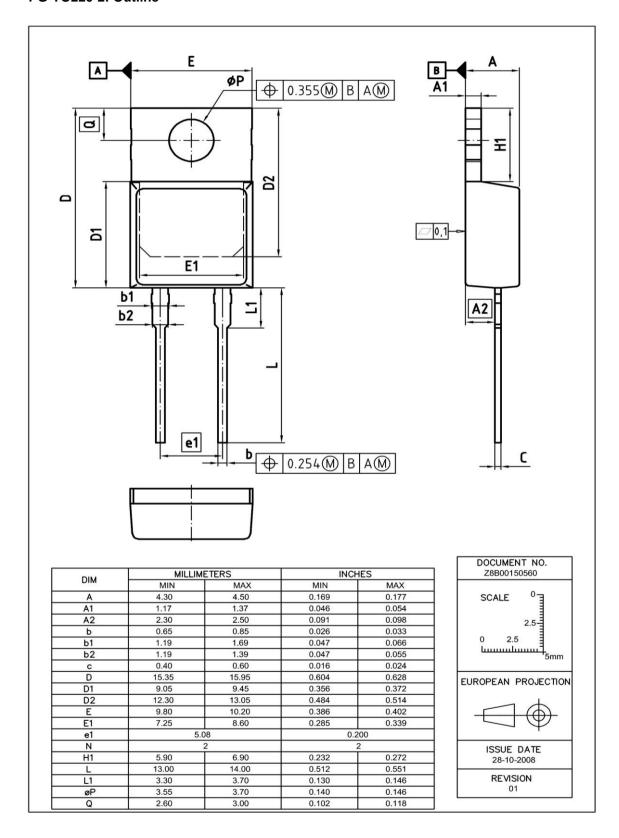
9 Typ. C stored energy

 $E_{C}=f(V_{R})$





PG-TO220-2: Outline



Dimensions in mm/inches



Published by Infineon Technologies AG 81726 Munich, Germany © 2012 Infineon Technologies AG All Rights Reserved.

Legal Disclaimer

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics. With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation, warranties of non-infringement of intellectual property rights of any third party.

Information

For further information on technology, delivery terms and conditions and prices, please contact the nearest Infineon Technologies Office (www.infineon.com).

Warnings

Due to technical requirements, components may contain dangerous substances. For information on the types in question, please contact the nearest Infineon Technologies Office. Infineon Technologies components may be used in life-support devices or systems and/or automotive, aviation and aerospace applications or systems only with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support, automotive, aviation and aerospace device or system or to affect the safety or effectiveness of that device or system. Life support systems are intended to be implanted in the human body and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.